Low-power dual Schmitt trigger Rev. 5 — 5 December 2011

Product data sheet

General description 1.

The 74AUP2G17 provides two Schmitt trigger buffers. It is capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \,\mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

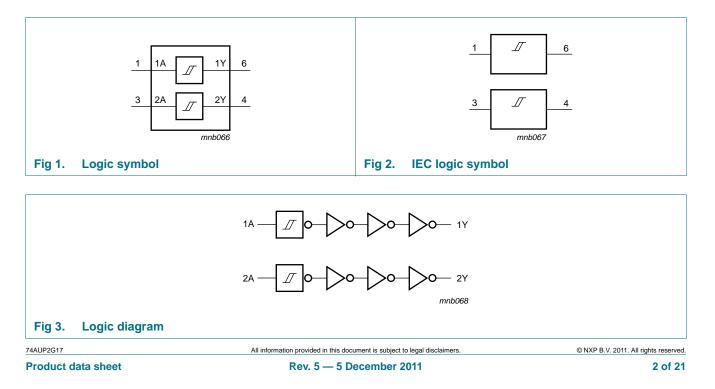
Table 1. Ordering	g information			
Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G17GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AUP2G17GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886
74AUP2G17GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891
74AUP2G17GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP2G17GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP2G17GW	pV
74AUP2G17GM	pV
74AUP2G17GF	pV
74AUP2G17GN	pV
74AUP2G17GS	pV

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

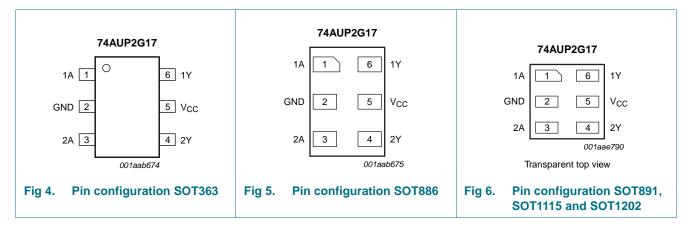
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output

7. Functional description

Table 4. Function table^[1]

Input	Output
nA	nY
L	L
Н	н

[1] H = HIGH voltage level; L = LOW voltage level.

Limiting values 8.

Limiting values Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					-
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

9. **Recommended operating conditions**

Table 6.	Recommended operating co	nditions			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C

10. Static characteristics

Table 7. **Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2						
V _{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; \text{ V}_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
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Symbol	Parameter	Conditions	Min	Тур	Мах	Uni
Vol	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V} \text{ to } 3.6 \ \text{V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA
\l _{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
сс	supply current	$\label{eq:VI} \begin{array}{l} V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A}; \\ V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \end{array} \qquad -$		-	0.5	μA
∕l ^{CC}	additional supply current		-	-	40	μA
C _I	input capacitance	$V_I = GND \text{ or } V_{CC}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	1.1	-	pF
C _o	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF
Г _{атb} = –	40 °C to +85 °C					
V _{он}	HIGH-level output voltage	$V_I = V_{T+} \text{ or } V_{T-}$				
		I_O = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
/ _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I	input leakage current	$V_{I} = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
OFF	power-off leakage current	$V_{\rm I}~{\rm or}~V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V	-	-	±0.5	μA

Table 7 Static characteristics ... continued

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current		-	-	±0.6	μA
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
Δl _{CC}	additional supply current		-	-	50	μA
T _{amb} = –	40 °C to +125 °C					
V _{он}	HIGH-level output voltage	$V_{I} = V_{T+} \text{ or } V_{T-}$				
		I_{O} = –20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{\text{CC}}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_0 = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 0.6 \; V; \; I_{O} = 0 \; A; \\ V_{CC} = 3.3 \; V \end{array}$	-	-	75	μΑ

Table 7. Static characteristics ...continued

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8

Symbol	Parameter	Conditions			25 °C		-4	0 °C to +1	25 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	F									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	19.0	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.6	5.7	10.6	2.5	10.9	11.1	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.4	4.2	6.5	2.3	7.1	7.4	ns
		V_{CC} = 1.65 V to 1.95 V		2.0	3.6	5.5	1.9	6.1	6.3	ns
		V_{CC} = 2.3 V to 2.7 V		1.9	3.0	4.2	1.8	4.6	4.8	ns
		V_{CC} = 3.0 V to 3.6 V		1.8	2.7	3.6	1.5	3.8	4.0	ns
C _L = 10	pF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	22.5	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.9	6.6	12.4	2.7	12.9	13.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.6	4.8	7.8	2.4	8.3	8.7	ns
		V _{CC} = 1.65 V to 1.95 V		2.5	4.2	6.3	2.4	6.8	7.1	ns
		V_{CC} = 2.3 V to 2.7 V		2.3	3.5	4.8	2.1	5.3	5.6	ns
		V_{CC} = 3.0 V to 3.6 V		2.1	3.3	4.4	2.0	4.6	4.8	ns
C _L = 15	pF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	26.0	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.2	7.4	14.1	3.1	14.7	14.9	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		3.1	5.4	8.7	2.8	9.5	9.9	ns
		V _{CC} = 1.65 V to 1.95 V		2.7	4.7	7.1	2.7	7.8	8.2	ns
		V_{CC} = 2.3 V to 2.7 V		2.6	4.0	5.6	2.5	6.0	6.3	ns
		V_{CC} = 3.0 V to 3.6 V		2.5	3.7	4.9	2.2	5.2	5.5	ns
C _L = 30	pF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	36.3	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.9	9.7	19.0	3.7	19.8	20.1	ns
		V_{CC} = 1.4 V to 1.6 V		3.5	7.0	11.2	3.6	12.4	13.0	ns
		V_{CC} = 1.65 V to 1.95 V		3.5	6.0	9.2	3.4	10.1	10.7	ns
		V_{CC} = 2.3 V to 2.7 V		3.4	5.1	7.0	3.2	7.5	7.9	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		3.3	4.8	6.2	3.1	7.1	7.5	ns

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		ND (ground = $0 V$); for test circuit se							
Symbol	Parameter	rameter Conditions		25 °C		-4	0 °C to +1	25 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Мах (85 °С)	Max (125 °C)	
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF							
C _{PD}	C _{PD} power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$ [3]							
		$V_{CC} = 0.8 V$	-	2.5	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	2.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	2.8	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	-	3.0	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	3.5	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	4.0	-	-	-	-	рF

Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\label{eq:PD} \mathsf{P}_{\mathsf{D}} = C_{\mathsf{PD}} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times f_i \times \mathsf{N} + \Sigma(C_\mathsf{L} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

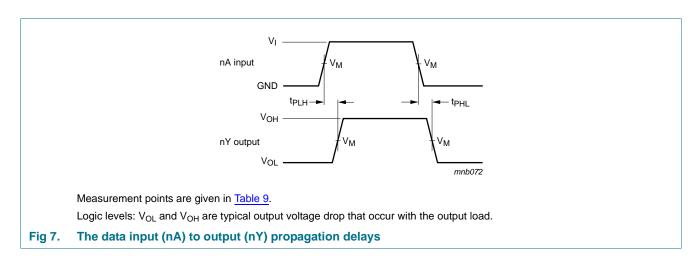


Table 9. **Measurement points**

Supply voltage	Output	Input				
V _{CC}	V _M	V _M	VI	t _r = t _f		
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5\times V_{CC}$	V _{CC}	≤ 3.0 ns		

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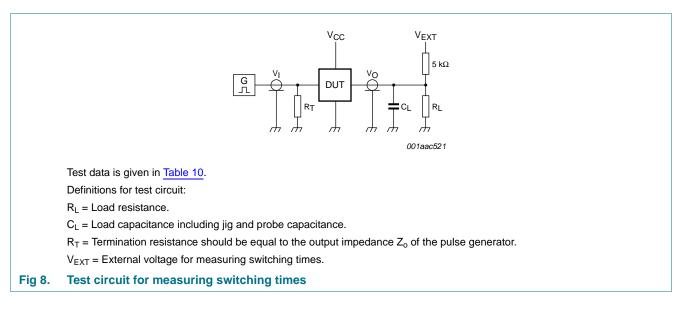


Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

13. Transfer characteristics

Table 11. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		
			Min	Тур	Мах	Min	Max (85 °C)	Max (125 °C)	
V _{T+} pos	positive-going	see Figure 9 and Figure 10							
	threshold voltage	$V_{CC} = 0.8 V$	0.30	-	0.60	0.30	0.60	0.62	V
		$V_{CC} = 1.1 V$	0.53	-	0.90	0.53	0.90	0.92	V
		V _{CC} = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V _{CC} = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		$V_{CC} = 2.3 V$	1.37	-	1.77	1.37	1.77	1.80	V
		$V_{CC} = 3.0 V$	1.88	-	2.29	1.88	2.29	2.32	V
	negative-going threshold voltage	see <u>Figure 9</u> and <u>Figure 10</u>							
		$V_{CC} = 0.8 V$	0.10	-	0.60	0.10	0.60	0.60	V
		V _{CC} = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		V _{CC} = 1.4 V	0.39	-	0.75	0.39	0.75	0.75	V
		V _{CC} = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		V_{CC} = 2.3 V	0.69	-	1.04	0.69	1.04	1.04	V
		$V_{CC} = 3.0 V$	0.88	-	1.24	0.88	1.24	1.24	V

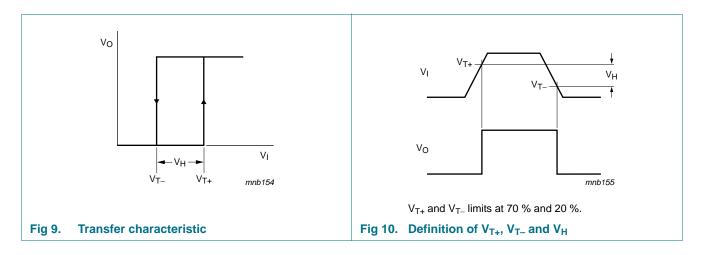
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Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		
			Min	Тур	Мах	Min	Max (85 °C)	Max (125 °C)	
V _H hysteresis voltage	hysteresis voltage	$(V_{T+} - V_{T-})$; see <u>Figure 9</u> , <u>Figure 10</u> , <u>Figure 11</u> and <u>Figure 12</u>							
	$V_{CC} = 0.8 V$	0.07	-	0.50	0.07	0.50	0.50	V	
		V _{CC} = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
	$V_{CC} = 1.4 V$	0.18	-	0.56	0.18	0.56	0.56	V	
	V _{CC} = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V	
	$V_{CC} = 2.3 V$	0.53	-	0.92	0.53	0.92	0.92	V	
		$V_{CC} = 3.0 V$	0.79	-	1.31	0.79	1.31	1.31	V

Table 11. Transfer characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see <u>Figure 8</u>.

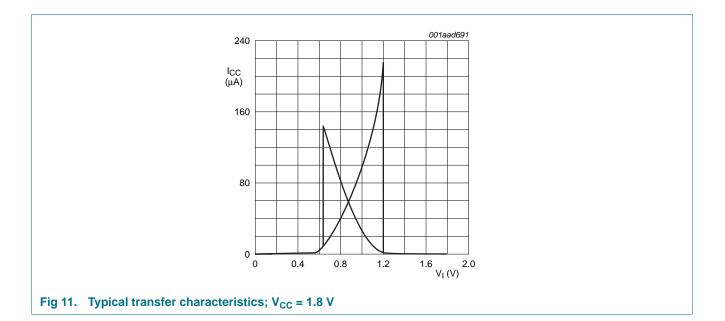
14. Waveforms transfer characteristics

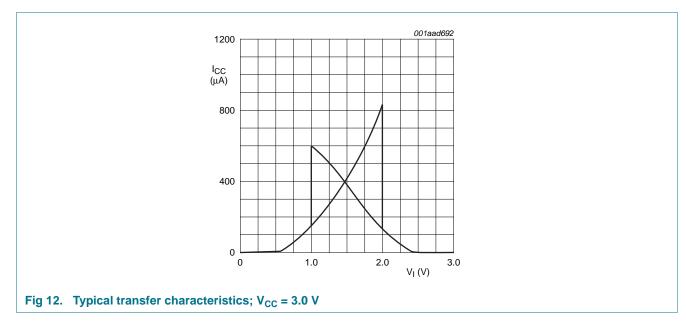


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15. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC} \text{ where:}$

 P_{add} = additional power dissipation (μ W);

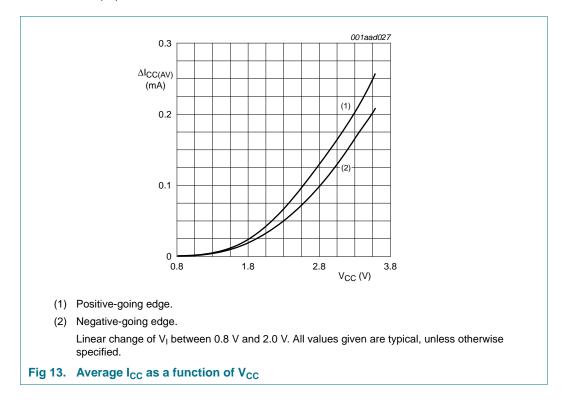
 $f_i = input frequency (MHz);$

 t_r = input rise time (ns); 10 % to 90 %;

 t_f = input fall time (ns); 90 % to 10 %;

 $\Delta I_{CC(AV)}$ = average additional supply current (µA).

Average $\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in Figure 13.



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16. Package outline

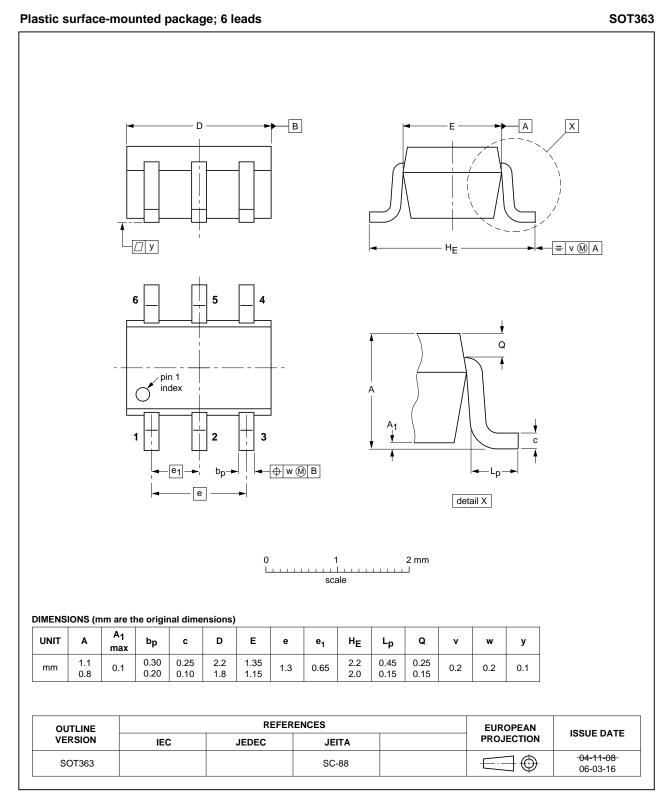


Fig 14. Package outline SOT363 (SC-88)

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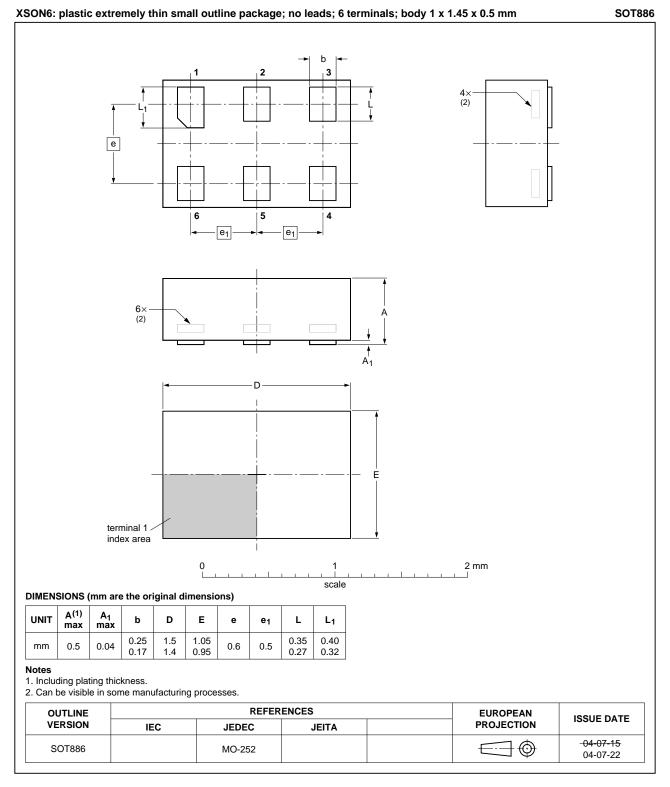


Fig 15. Package outline SOT886 (XSON6)

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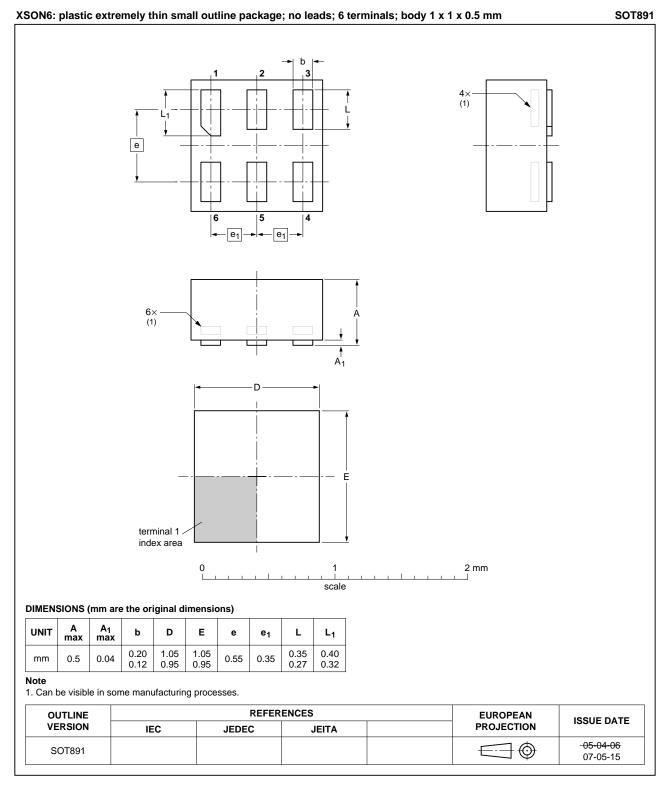
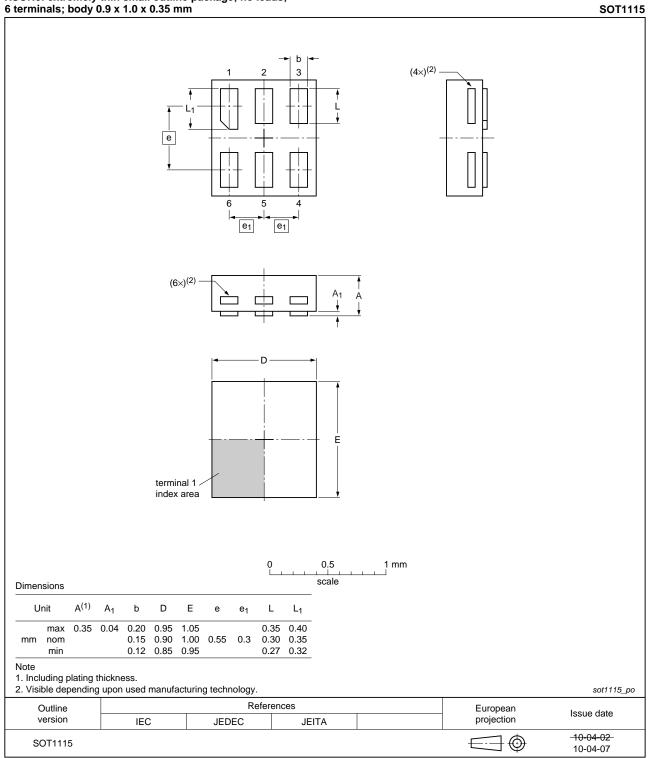


Fig 16. Package outline SOT891 (XSON6)

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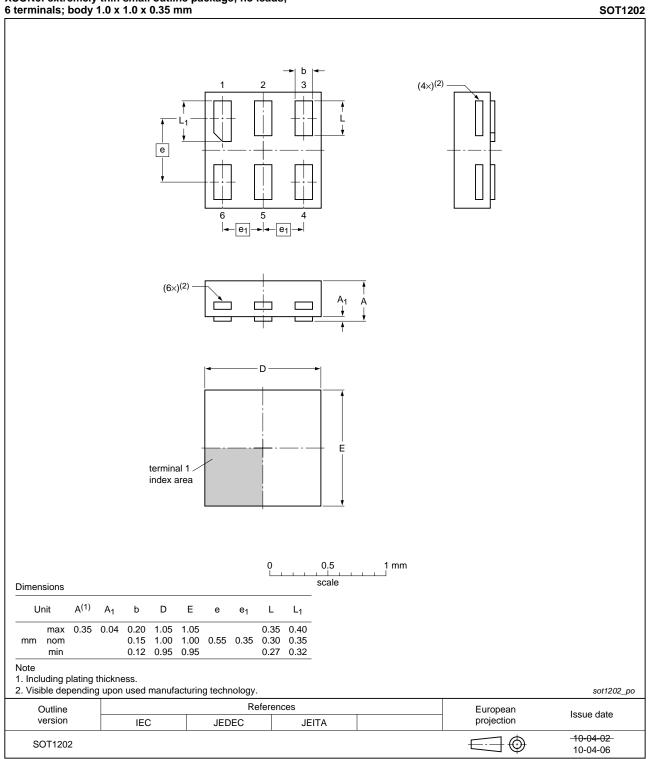
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 18. Package outline SOT1202 (XSON6)

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17. Abbreviations

Table 12. Abbreviations			
Acronym	Description		
CDM	Charged Device Model		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
MM	Machine Model		

18. Revision history

Table 13.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G17 v.5	20111205	Product data sheet	-	74AUP2G17 v.4
Modifications:	 Legal pages 	s updated.		
74AUP2G17 v.4	20101103	Product data sheet	-	74AUP2G17 v.3
74AUP2G17 v.3	20090706	Product data sheet	-	74AUP2G17 v.2
74AUP2G17 v.2	20080110	Product data sheet	-	74AUP2G17 v.1
74AUP2G17 v.1	20061107	Product data sheet	-	-

19. Legal information

19.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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